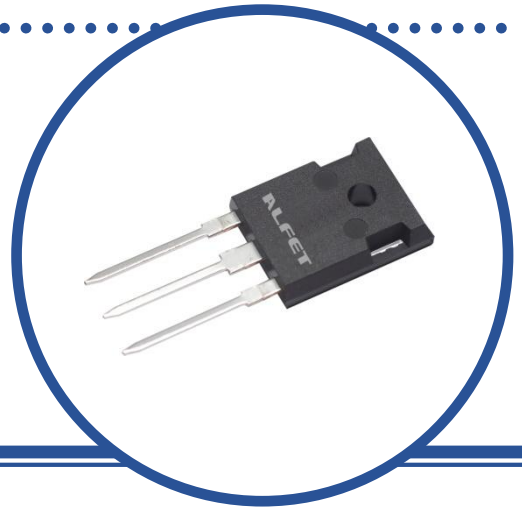


N-CHANNEL LATERAL POWER MOSFET FOR AUDIO

ALF08N16V/ALF08N20V

- Designed specifically for linear audio amplifier applications
- High-speed for high bandwidth amplifiers
- High voltage rating – 160V & 200V
- TO-247 plastic package
- Enhanced oscillation suppression in multi-device applications
- Complimentary P-channel available – ALF08P16V/ALF08P20V



ABSOLUTE MAXIMUM RATINGS

($T_C = 25^\circ\text{C}$ unless otherwise stated)

		ALF08N16V	ALF08N20V
V_{DSS}	Drain – Source Voltage	160V	200V
V_{GSS}	Gate – Source Voltage	$\pm 20\text{V}$	
I_D	Continuous Drain Current	8A	
I_{DR}	Body Drain Diode Current	8A	
P_D	Allowable Power Dissipation $T_{\text{case}} = 25^\circ\text{C}$	125W	
T_{ch}	Channel Temperature	150°C	
T_{stg}	Storage Temperature Range	-55 to +150°C	

THERMAL PROPERTIES

Symbols	Parameters	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction To Case			1	$^\circ\text{C/W}$

Magnatec reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Magnatec is believed to be both accurate and reliable at the time of going to press. However Magnatec assumes no responsibility for any errors or omissions discovered in its use. Magnatec encourages customers to verify that datasheets are current before placing orders.

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ALF08N16V/ALF08N20V

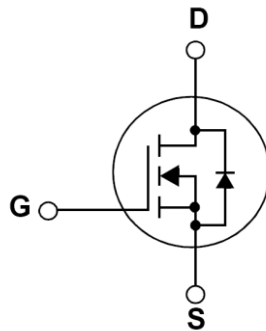
ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
BV_{DSX}	Drain-Source Breakdown Voltage	$V_{GS} = -10\text{V}$ $I_D = 10\text{mA}$	ALF08N16V	160		V
			ALF08N20V	200		
BV_{GSS}	Gate-Source Breakdown Voltage	$V_{DS} = 0$ $I_G = \pm 100 \mu\text{A}$	± 20			V
$V_{GS(off)}$	Gate-Source Cut-off Voltage	$V_{DS} = 10\text{V}$ $I_D = 100\text{mA}$	0.15		1.5	V
$V_{DS(sat)*}$	Drain-Source Saturation Voltage	$V_{GD} = 0$ $I_D = 8\text{A}$			12	V
$ y_{fs} ^*$	Forward Transfer Admittance	$V_{DS} = 10\text{V}$ $I_{DS} = 3\text{A}$	0.7		2	S(Ω)
I_{DSX}	Drain-Source Cut-Off Current	$V_{GS} = -10\text{V}$	$V_{DS} = 160\text{V}$ ALF08N16V		10	mA
			$V_{DS} = 200\text{V}$ ALF08N20V		10	

* Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2\%$

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{GS} = 0$		500		pF
C_{oss}	Output Capacitance	$V_{DS} = 10\text{V}$		300		
C_{rss}	Reverse Transfer Capacitance	$f = 1.0\text{MHz}$		10		
t_{on}	Turn-On Time	$V_{DS} = 20\text{V}$		100		ns
t_{off}	Turn-Off Time	$I_D = 5\text{A}$		50		

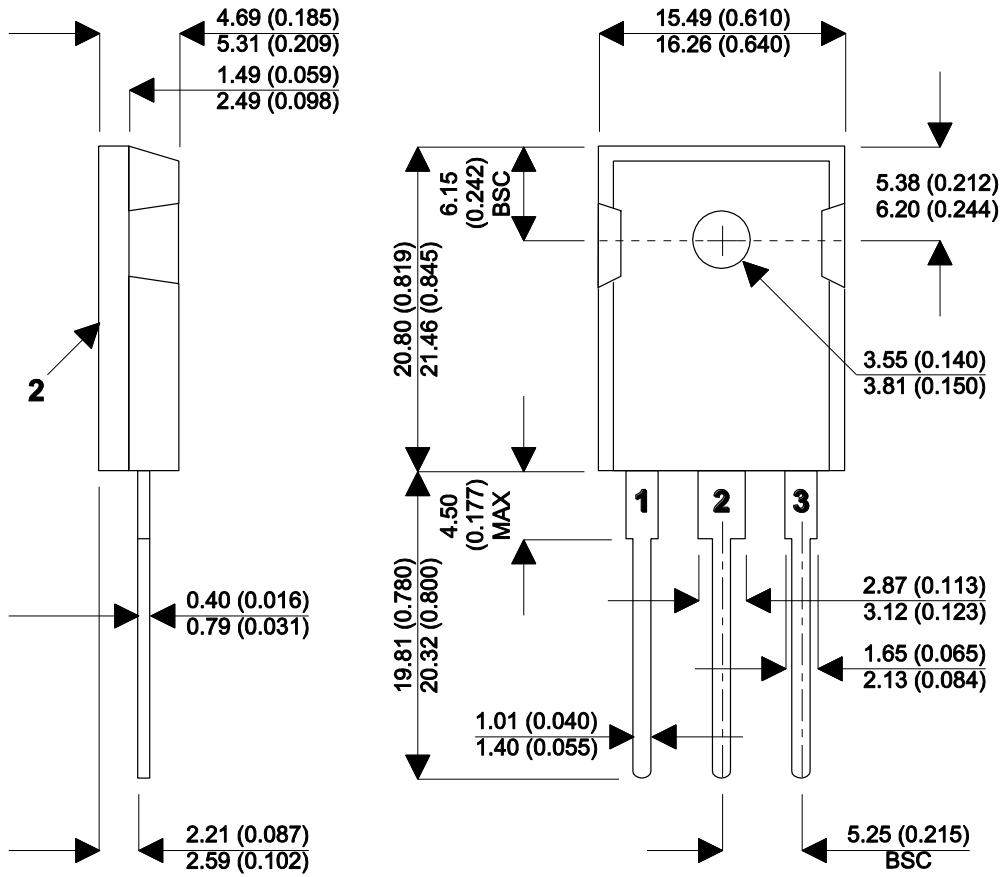


Please Note: These lateral mosfets do not include a G-S protection network and care must therefore be taken with static handling precautions and the appropriate protection in the amplifier circuit. Please refer to the application notes for more information.

ALF08N16V/ALF08N20V

MECHANICAL DATA

Dimensions in mm



TO-247

Pin 1 - Gate

Pin 2 -Source

Pin 3 – Drain